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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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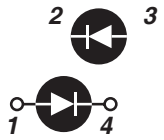
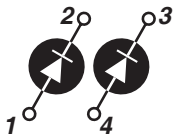


Anti-Parallel
APT2X60D20J



Parallel
APT2X61D20J

ISOTOP®

ADVANCED POWER TECHNOLOGY®

APT2X61D20J 200V 60A
APT2X60D20J 200V 60A

DUAL DIE ISOTOP® PACKAGE
ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

PRODUCT APPLICATIONS

- **Anti-Parallel Diode**
  - **-Switchmode Power Supply**
  - **-Inverters**
- **Free Wheeling Diode**
  - **-Motor Controllers**
  - **-Converters**
- **Snubber Diode**
- **Uninterruptible Power Supply (UPS)**
- **Induction Heating**
- **High Speed Rectifiers**

PRODUCT FEATURES

- **Ultrafast Recovery Times**
- **Soft Recovery Characteristics**
- **Popular SOT-227 Package**
- **Low Forward Voltage**
- **High Blocking Voltage**
- **Low Leakage Current**

PRODUCT BENEFITS

- **Low Losses**
- **Low Noise Switching**
- **Cooler Operation**
- **Higher Reliability Systems**
- **Increased System Power Density**

MAXIMUM RATINGS All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT2X61_60D20J	UNIT
V_R	Maximum D.C. Reverse Voltage	200	Volts
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
V_{RWM}	Maximum Working Peak Reverse Voltage		
$I_{F(AV)}$	Maximum Average Forward Current (T_C = 122°C, Duty Cycle = 0.5)	60	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	107	
I_{FSM}	Non-Repetitive Forward Surge Current (T_J = 45°C, 8.3ms)	600	
T_J,T_{STG}	Operating and StorageTemperature Range	-55 to 175	°C
T_L	Lead Temperature for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
V_F	Forward Voltage	I_F = 60A		1.1	1.3	Volts
		I_F = 120A		1.4		
		I_F = 60A, T_J = 125°C		0.9		
I_{RM}	Maximum Reverse Leakage Current	V_R = V_R Rated			250	µA
		V_R = V_R Rated, T_J = 125°C			500	
C_T	Junction Capacitance, V_R = 200V			210		pF

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DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	I_F = 1A, di_F/dt = -100A/µs, V_R = 30V, T_J = 25°C	-	30		ns
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -200A/µs, V_R = 133V, T_C = 25°C	-	31		ns
Q_{rr}	Reverse Recovery Charge		-	60		nC
I_{RRM}	Maximum Reverse Recovery Current		-	3	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -200A/µs, V_R = 133V, T_C = 125°C	-	60		ns
Q_{rr}	Reverse Recovery Charge		-	250		nC
I_{RRM}	Maximum Reverse Recovery Current		-	7	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -1000A/µs, V_R = 133V, T_C = 125°C	-	40		ns
Q_{rr}	Reverse Recovery Charge		-	540		nC
I_{RRM}	Maximum Reverse Recovery Current		-	24		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			.60	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			20	
W_T	Package Weight		1.03		oz
			29.2		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

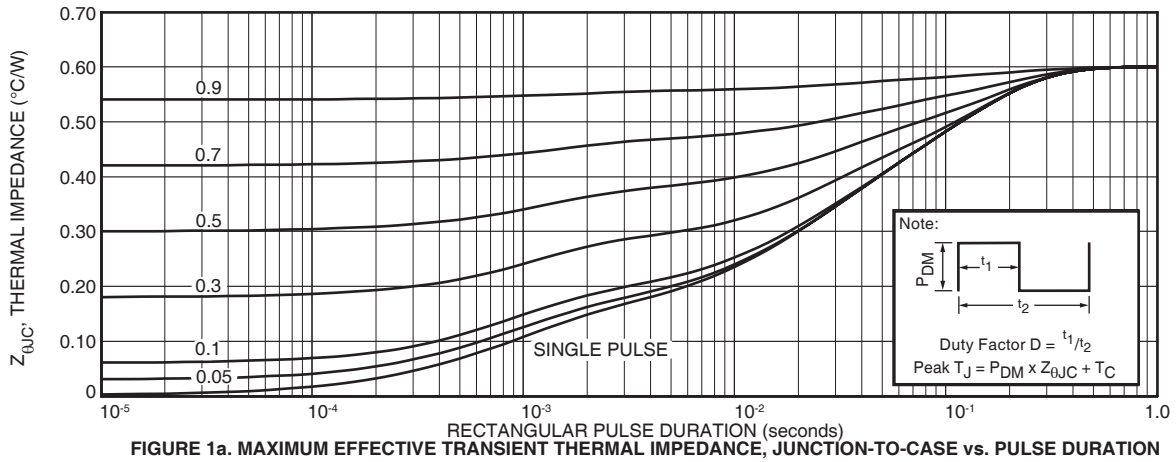


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

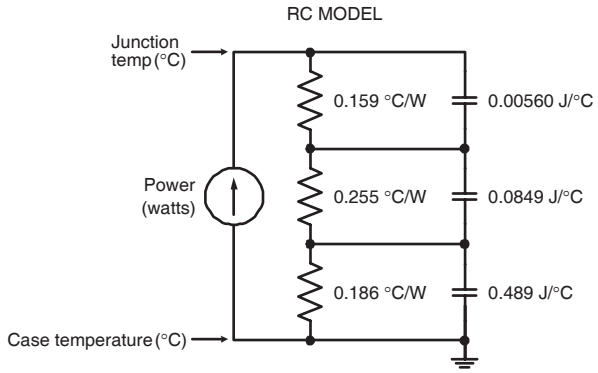


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

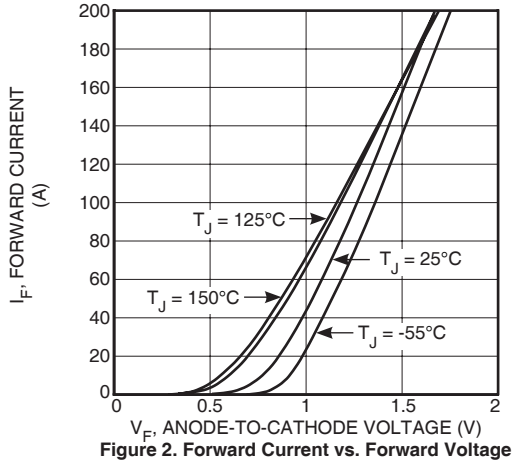


Figure 2. Forward Current vs. Forward Voltage

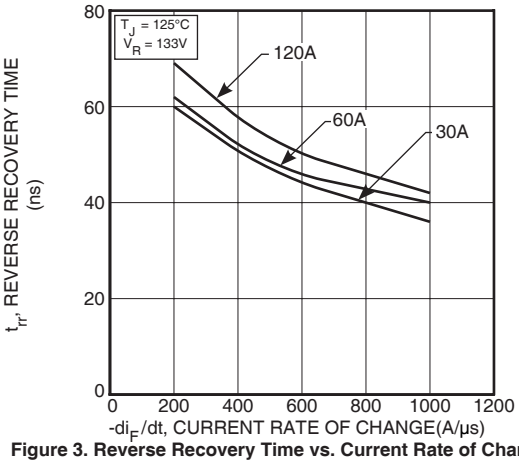


Figure 3. Reverse Recovery Time vs. Current Rate of Change

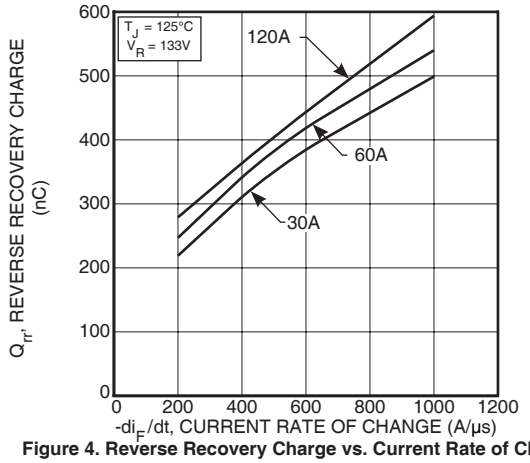


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

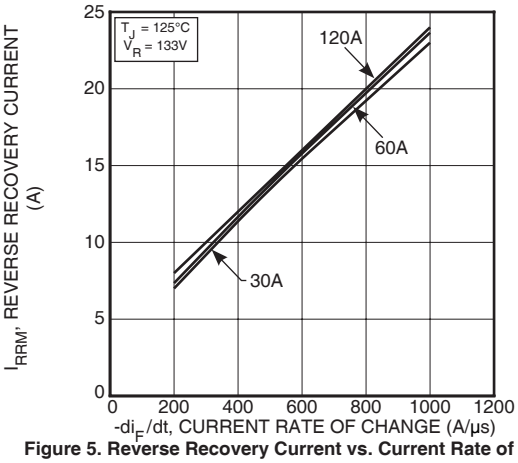


Figure 5. Reverse Recovery Current vs. Current Rate of Change

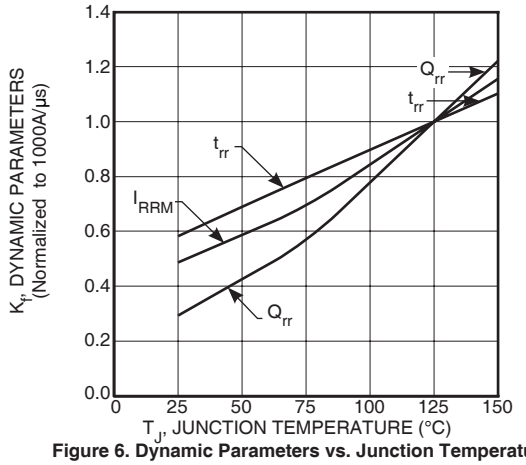


Figure 6. Dynamic Parameters vs. Junction Temperature

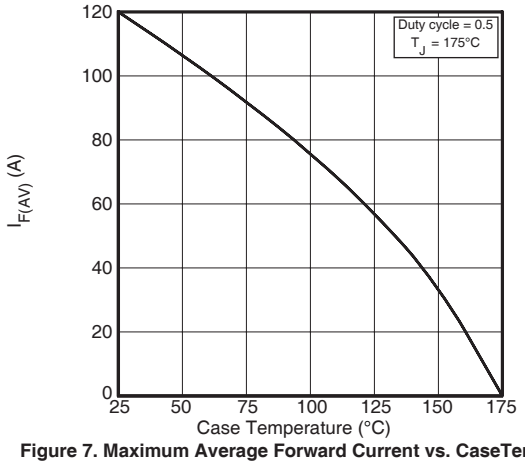


Figure 7. Maximum Average Forward Current vs. CaseTemperature

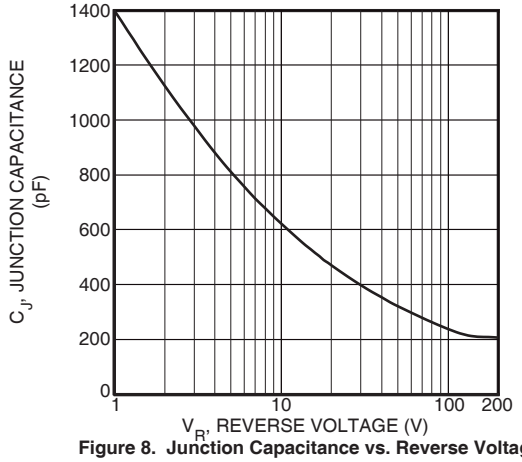


Figure 8. Junction Capacitance vs. Reverse Voltage

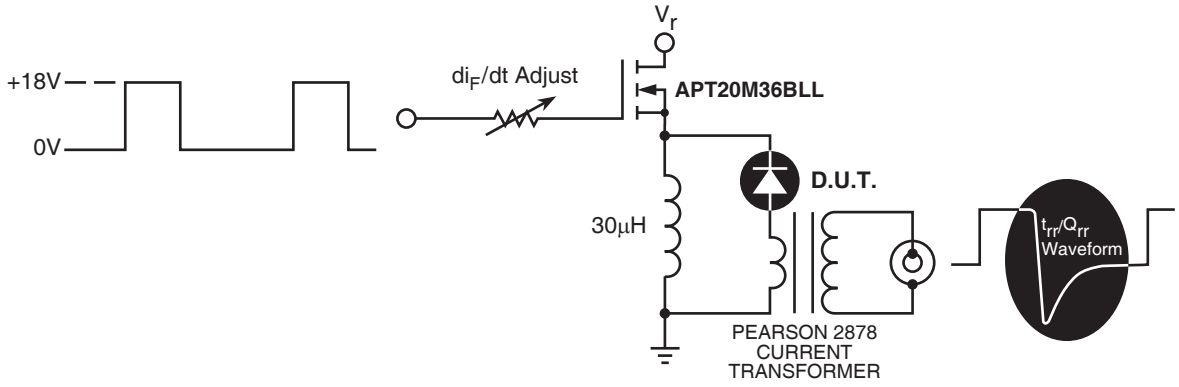
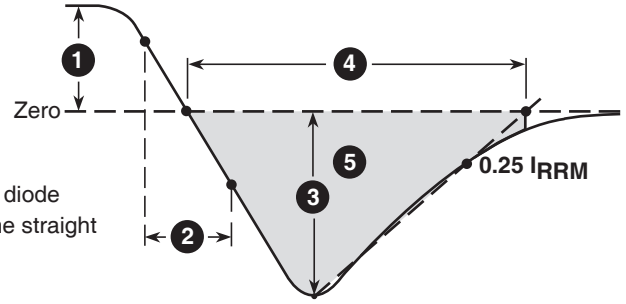


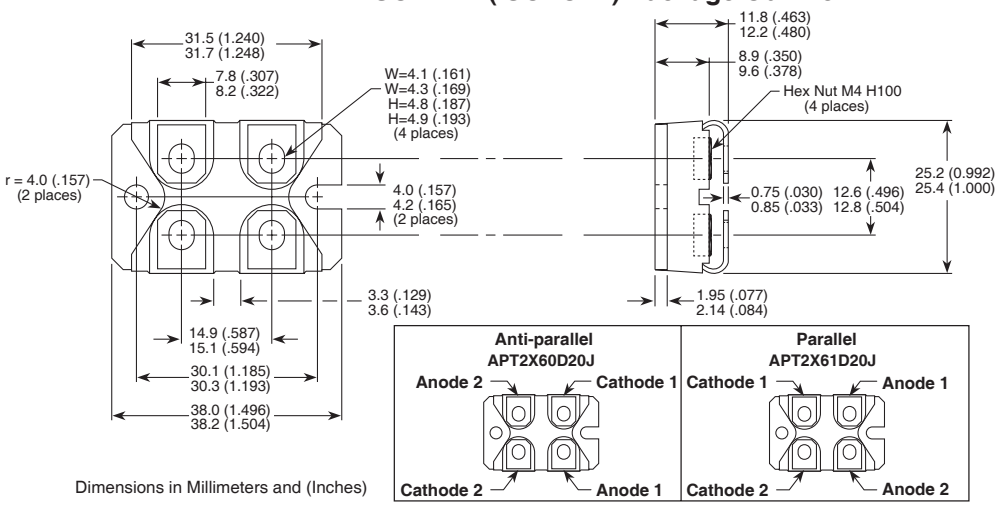
Figure 9. Diode Test Circuit



1. I_F - Forward Conduction Current
2. di_F/dt - Rate of Diode Current Change Through Zero Crossing.
3. I_{RRM} - Maximum Reverse Recovery Current.
4. t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \bullet I_{RRM}$ passes through zero.
5. Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr}.

Figure 10, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

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